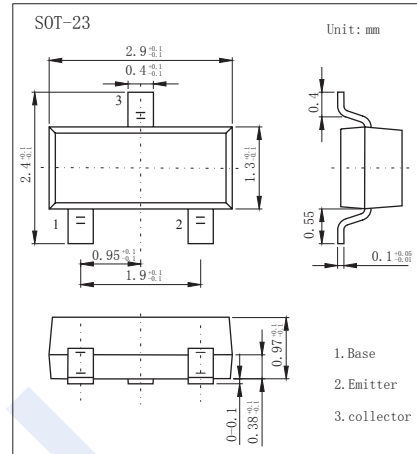


PNP Transistors

2SA1566

- Features
- Low frequency amplifier



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-120	V
Collector - Emitter Voltage	V_{CE0}	-120	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}$, $R_{BE} = \infty$	-120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -70 \text{ V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4 \text{ V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	$I_C = -10 \text{ mA}$, $I_B = -1 \text{ mA}$			-0.15	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	$I_C = -10 \text{ mA}$, $I_B = -1 \text{ mA}$			-1	
DC current gain (Note.1)	h_{FE}	$V_{CE} = -12 \text{ V}$, $I_C = -2 \text{ mA}$	250		800	

Note.1: Pulse test

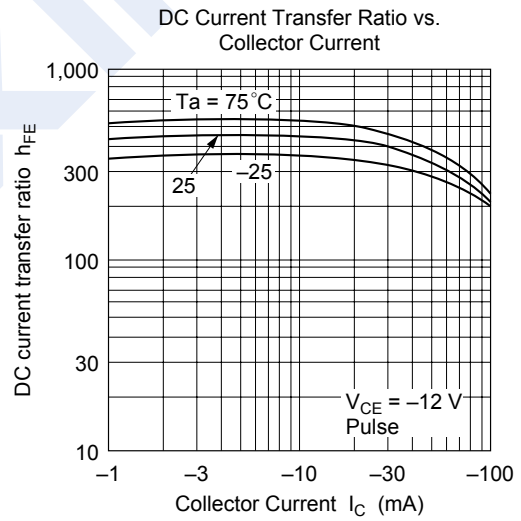
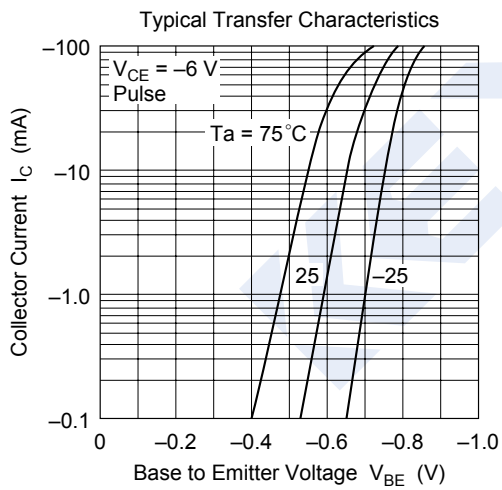
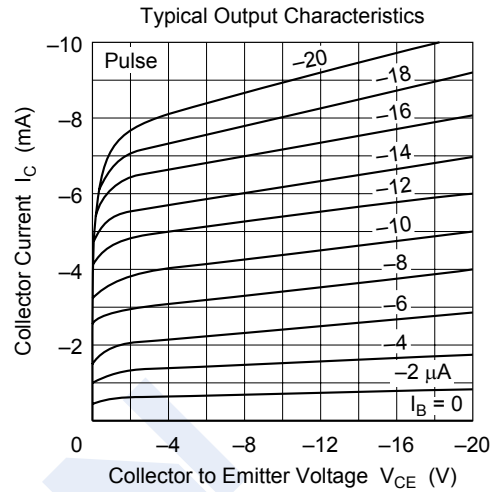
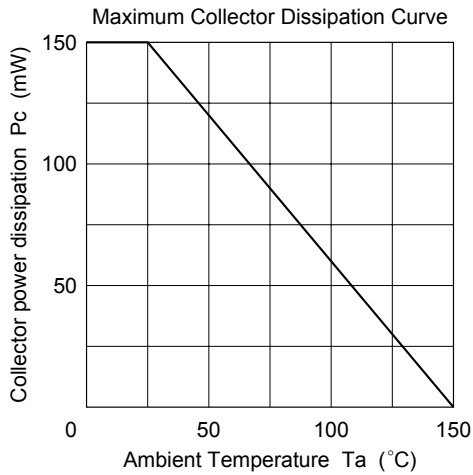
■ Classification of h_{FE}

Type	2SA1566-D	2SA1566-E
Range	250-500	400-800
Marking	JID	JIE

PNP Transistors

2SA1566

■ Typical Characteristics



PNP Transistors

2SA1566

■ Typical Characteristics

